2SC5250

Silicon NPN Triple Diffused Planar

HITACHI

Preliminary

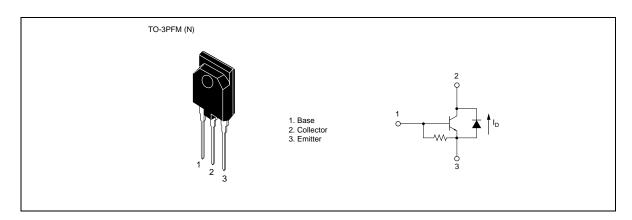
Application

Character display horizontal deflection output

Features

- High breakdown voltage
 - $V_{\scriptscriptstyle CBO}=1500~V$
- High speed switching
 - $t_f = 0.2 \, \mu sec \, (typ)$
- Built-in damper diode type
- Isolated package TO-3P•FM (N)

Outline



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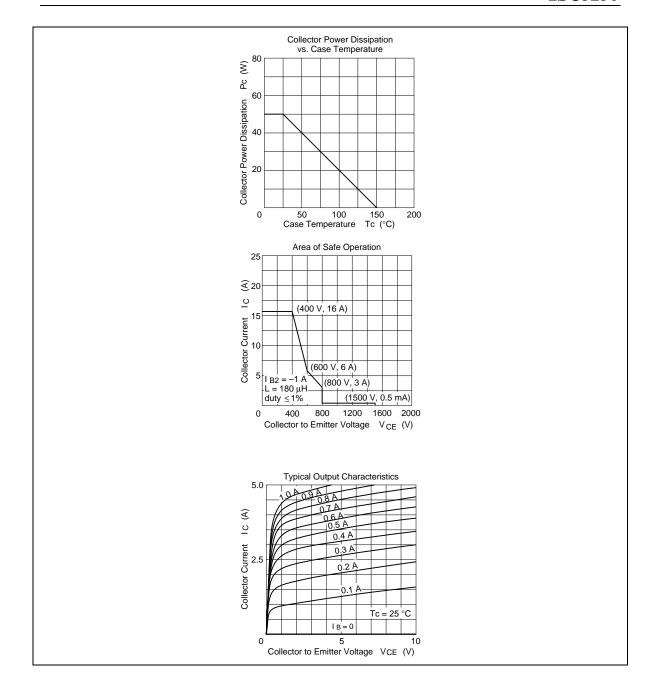
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

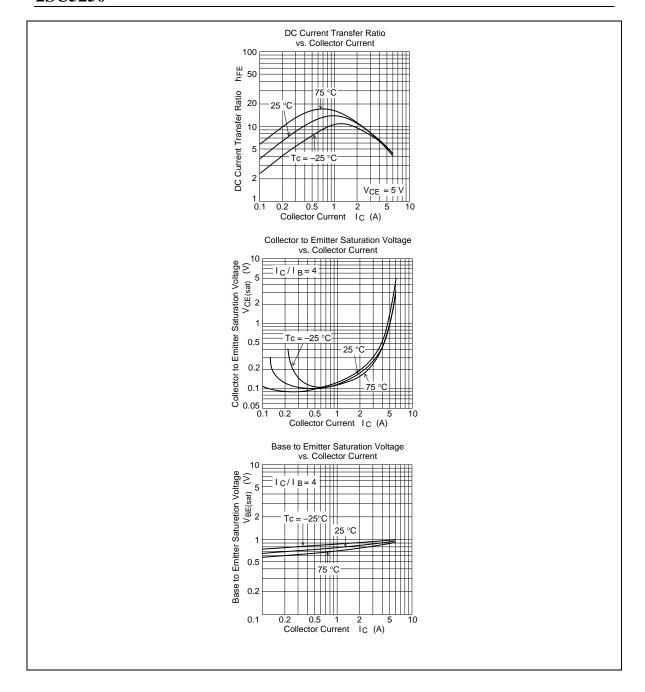
Item	Symbol	Ratings	Unit
Collector to emitter voltage	V _{CES}	1500	V
Emitter to base voltage	$V_{\scriptscriptstyle{EBO}}$	6	V
Collector current	I _c	8	A
Collector peak current	C(peak)	16	A
Collector power dissipation	P _c *1	50	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
Diode current	I _D	8	A

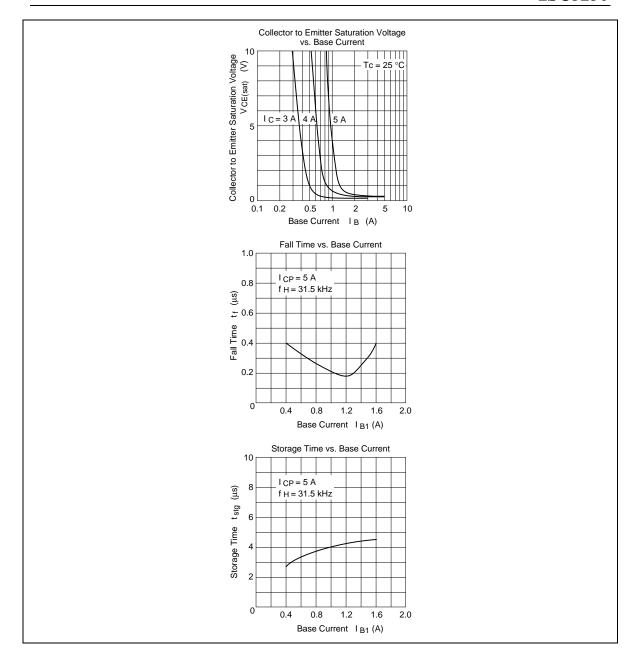
Note: 1. Value at $T_c = 25^{\circ}C$

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Emitter to base breakdown voltage	$V_{\text{(BR)EBO}}$	6	_	_	V	$I_{\rm E} = 400 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CES}	_	_	500	μΑ	V _{CE} = 1500 V, R _{BE} = 0
DC current transfer ratio	$h_{{\scriptscriptstyle FE1}}$	6	_	25		$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$
DC current transfer ratio	$h_{\scriptscriptstyleFE2}$	4	_	7		$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ A}$
Collector to emitter saturation voltage	$V_{\scriptscriptstyle{CE(sat)}}$	_	_	5	V	$I_{c} = 5 \text{ A}, I_{B} = 1.25 \text{ A}$
Base to emitter saturation voltage	$V_{\scriptscriptstyle{BE(sat)}}$	_	_	1.5	V	$I_{c} = 5 \text{ A}, I_{B} = 1.25 \text{ A}$
Forward voltage of damper diode	V_{ECF}	_	_	2	V	I _F = 8 A
Fall time	t _f	_	0.2	0.4	µsec	$I_{CP} = 5 \text{ A}, I_{B1} = 1 \text{ A},$ $f_{H} = 31.5 \text{ kHz}$







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